

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method for forming a pattern over a substrate, comprising:
 - providing a master having at least one opening;
 - providing a substrate having an etching layer formed thereon, the etching layer having at least one stepped portion;
 - locating the master over the etching layer, the master being separated from the substrate at a distance;
 - filling a resist in the at least one opening of the master on the etching layer having at least one stepped portion;
 - hardening the resist by applying ~~the~~ a heat or an ultraviolet ray to the resist;
 - moving away the master from the substrate to leave the resist on the substrate to form a resist pattern; and
 - etching the etching layer using the resist pattern as a mask,
 - wherein the master is separated from the substrate by a few micrometers (μm) during filling the resist in opening of the master.
2. (Original) The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - contacting a resist supplying roll to the master; and
 - filling the resist in the at least one opening of the master by rotating the resist supplying roll over the at least one opening of the master.
3. (Original) The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - applying the resist on the master; and
 - planarizing the applied resist on the surface of the master by using a doctor blade.

4. (Cancelled)
5. (Original) The method of claim 1, wherein the etching layer is a metal layer.
6. (Original) The method of claim 1, wherein the etching layer is an insulating layer.
7. (Original) The method of claim 6, wherein the insulating layer is formed of one of SiO_x or SiN_x.
8. (Original) The method of claim 1, wherein the etching layer is a semiconductor layer.
9. (Original) The method of claim 1, further comprising hardening the resist.
10. (Currently Amended) A method for forming a pattern over a substrate, comprising:
 - providing a master having at least one opening;
 - providing a substrate having an etching layer formed thereon, the etching layer having at least one stepped portion;
 - placing the master over an area corresponding to the etching layer to be etched, the master being separated from the substrate at a distance;
 - applying a resist on the master;
 - planarizing the applied resist on the surface of the master and filling the resist in the at least one opening on the etching layer having at least one stepped portion by using a doctor blade;
 - hardening the planarized resist by applying ~~the~~ a heat or an ultraviolet ray to the resist;
 - forming a resist pattern on the etching layer by separating the master from the substrate; and
 - etching the etching layer using the resist pattern as a mask, wherein the master is separated from the substrate by a few micrometers (μm) during

filling the resist in opening of the master.

11. (Cancelled)

12. (Currently Amended) A method for forming a pattern over a substrate, comprising:

providing a master having at least one opening

providing a substrate having an etching layer formed thereon, the etching layer having at least one stepped portion;

placing the master over the etching layer, the opening of the master being corresponding to the etching region to be etched;

contacting a resist supplying roll on the master to fill the resist in the at least one opening of the master on the etching layer having at least one stepped portion, the master being separated from the substrate at a distance;

hardening the filled resist in the at least one opening of the master by applying the heat or ultraviolet ray to the resist; and

forming a resist pattern on the etching layer by separating ~~mechanically~~ the master from the substrate; and

etching the etching layer using the resist pattern as a mask,

wherein the master is separated from the substrate by a few micrometers (μm) during filling the resist in opening of the master.

13. (Cancelled)

14. (Previously Presented) The method of claim 1, wherein the master is separated from the substrate by 1-9 μm during filling the resist in opening of the master.

15. (Previously Presented) The method of claim 1, the master is separated from the substrate by several micrometers (μm) during filling the resist in opening of the master.

16. (Previously Presented) The method of claim 10, wherein the master is

separated from the substrate by 1-9 μm during filling the resist in opening of the master.

17. (Previously Presented) The method of claim 10, the master is separated from the substrate by several micrometers (μm) during filling the resist in opening of the master.

18. (Previously Presented) The method of claim 12, wherein the master is separated from the substrate by 1-9 μm during filling the resist in opening of the master.

19. (Previously Presented) The method of claim 12, the master is separated from the substrate by several micrometers (μm) during filling the resist in opening of the master.